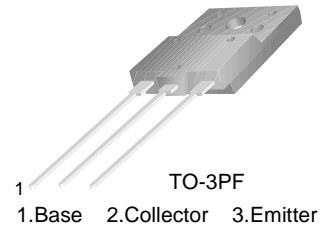


TIP140F/141F/142F

Monolithic Construction With Built In Base-Emitter Shunt Resistors

- Complement to TIP145F/146F/147F
- High DC Current Gain : $h_{FE} = 1000$ @ $V_{CE} = 4V, I_C = 5A$ (Min.)
- Industrial Use

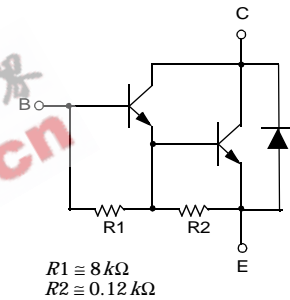


NPN Epitaxial Darlington Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage : TIP140F	60	V
	: TIP141F	80	V
	: TIP142F	100	V
V_{CEO}	Collector-Emitter Voltage : TIP140F	60	V
	: TIP141F	80	V
	: TIP142F	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current (DC)	10	A
I_{CP}	Collector Current (Pulse)	15	A
I_B	Base Current (DC)	0.5	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	60	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

Equivalent Circuit



Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	$I_C = 30\text{mA}, I_B = 0$	60			V
	: TIP140F					
	: TIP141F					
I_{CEO}	Collector Cut-off Current	$V_{CE} = 30\text{V}, I_B = 0$ $V_{CE} = 40\text{V}, I_B = 0$ $V_{CE} = 50\text{V}, I_B = 0$			2	mA
	: TIP140F					
	: TIP141F					
I_{CBO}	Collector Cut-off Current	$V_{CB} = 60\text{V}, I_E = 0$ $V_{CB} = 80\text{V}, I_E = 0$ $V_{CB} = 100\text{V}, I_E = 0$			1	mA
	: TIP140F					
	: TIP141F					
I_{EBO}	Emitter Cut-off Current	$V_{BE} = 5\text{V}, I_C = 0$			2	mA
h_{FE}	DC Current Gain	$V_{CE} = 4\text{V}, I_C = 5\text{A}$ $V_{CE} = 4\text{V}, I_C = 10\text{A}$	1000			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 5\text{A}, I_B = 10\text{mA}$ $I_C = 10\text{A}, I_B = 40\text{mA}$			2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10\text{A}, I_B = 40\text{mA}$			3.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 4\text{V}, I_C = 10\text{A}$			3	V
t_D	Delay Time	$V_{CC} = 30\text{V}, I_C = 5\text{A}$ $I_{B1} = 20\text{mA}, I_{B2} = -20\text{mA}$ $R_L = 6\Omega$			0.15	μs
t_R	Rise Time					
t_{STG}	Storage Time					
t_F	Fall Time					
					2.5	μs
					2.5	μs

Typical Characteristics

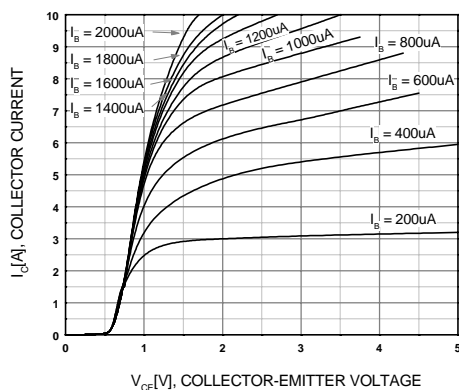


Figure 1. Static Characteristics

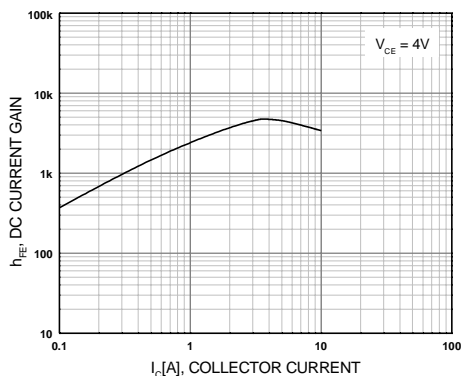


Figure 2. DC current Gain

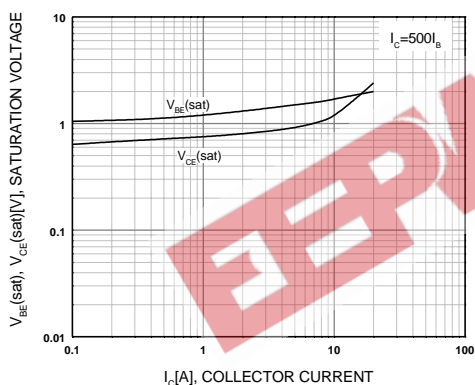


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

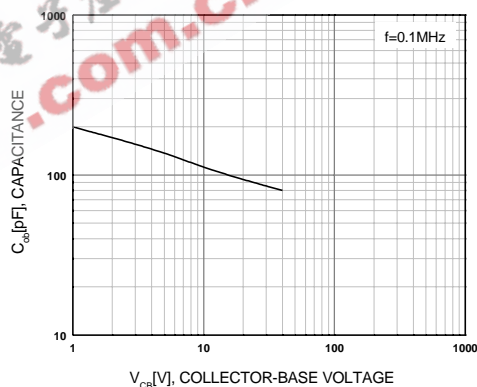


Figure 4. Collector Output Capacitance

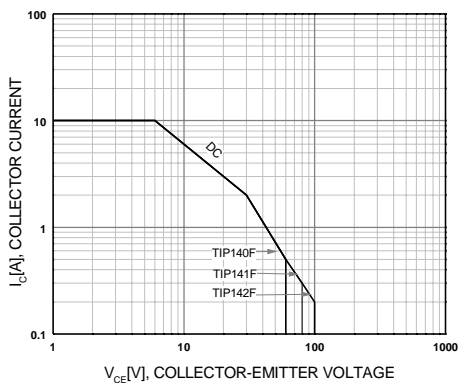


Figure 5. Safe Operating Area

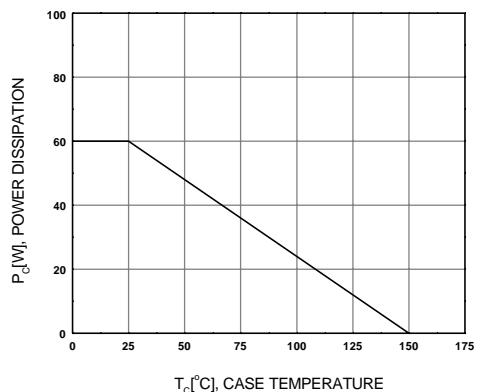
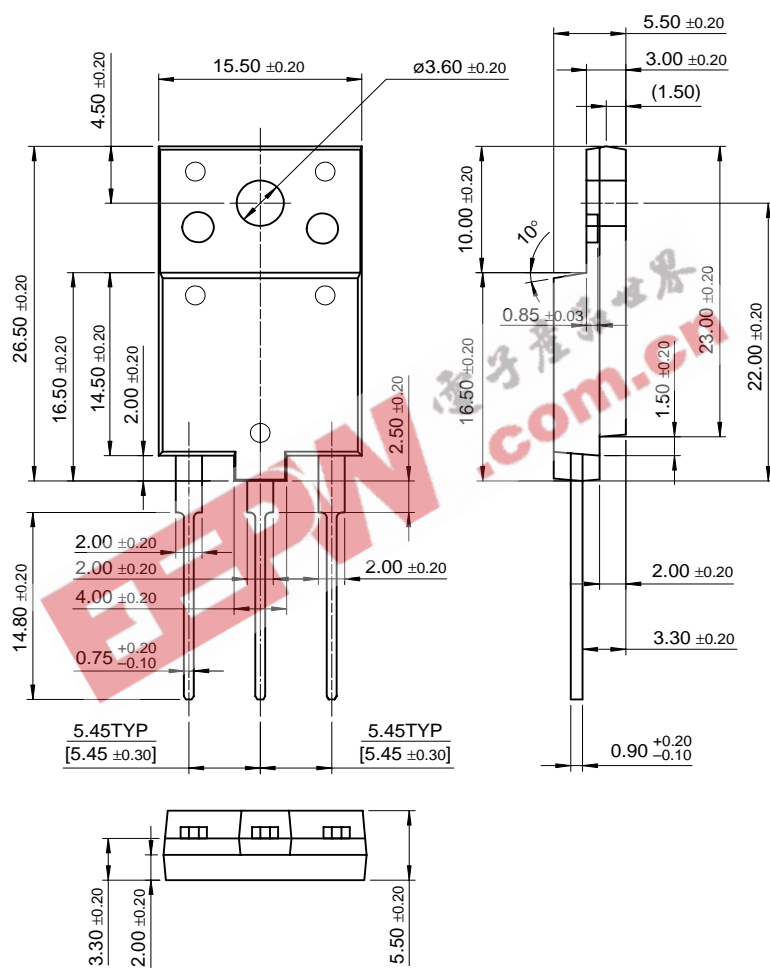


Figure 6. Power Derating

Package Dimensions

TO-3PF



Dimensions in Millimeters

TIP140F/141F/142F

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CoolFET™	FASTr™	MicroFET™	PowerTrench®	SuperSOT™-6
CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
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